

1 / 16

FIG. 1

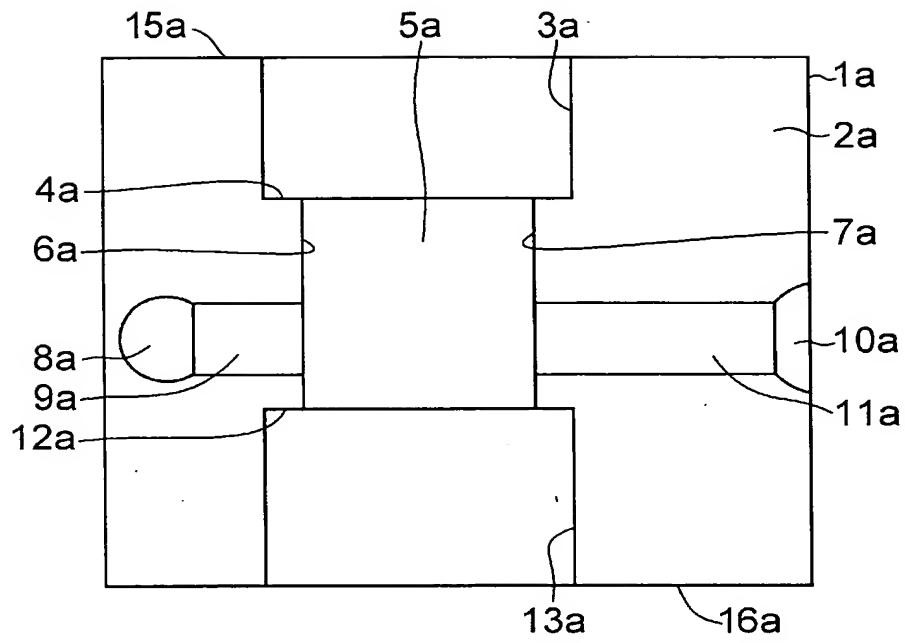
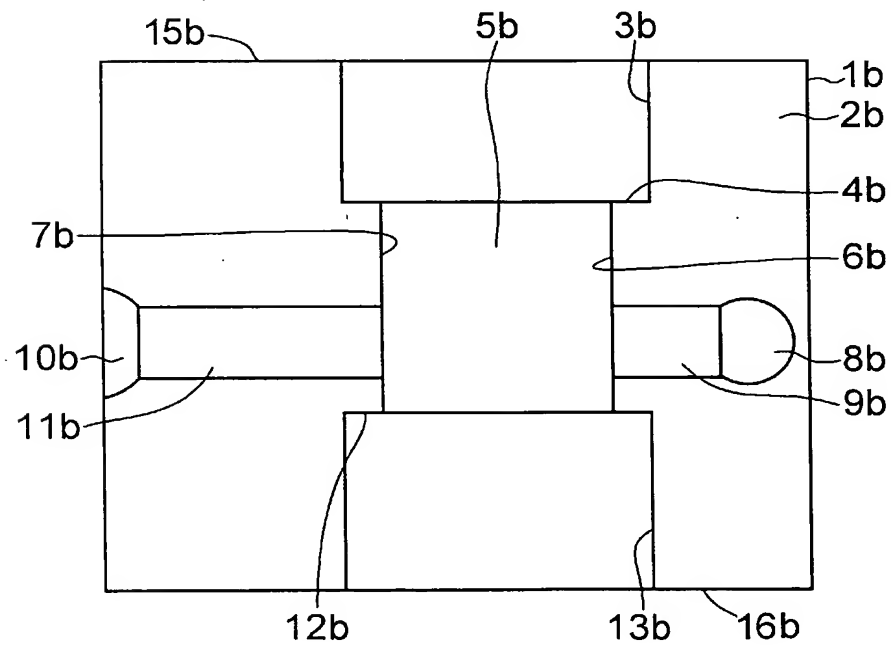


FIG. 2



2 / 16

FIG. 3

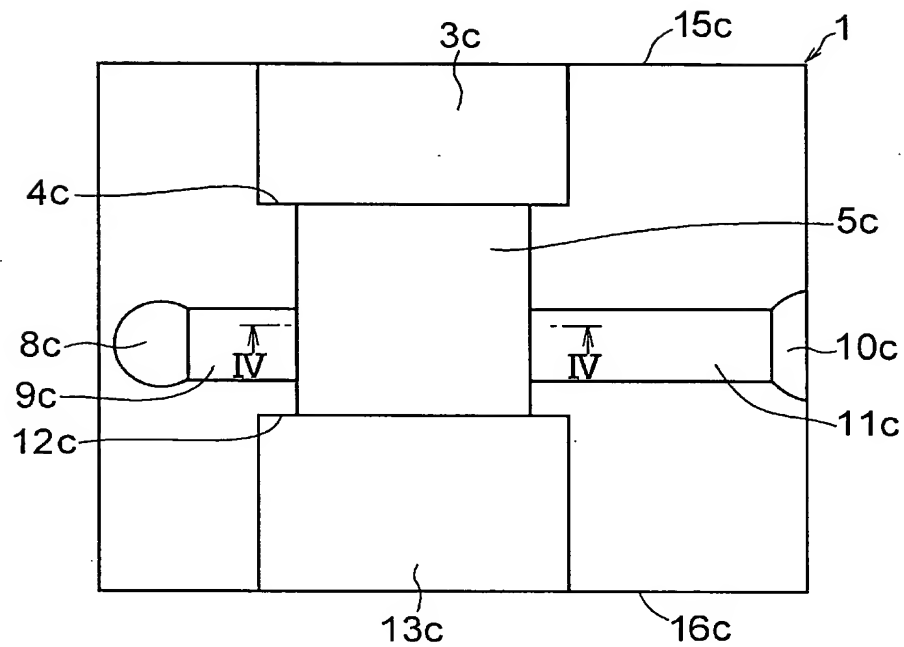
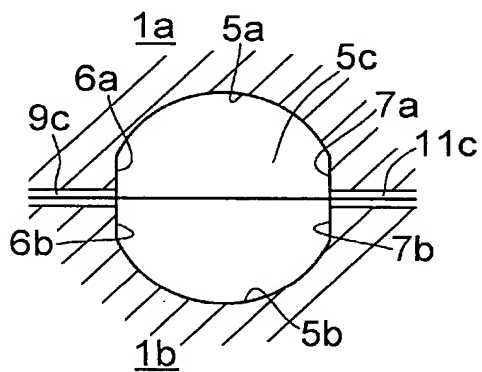


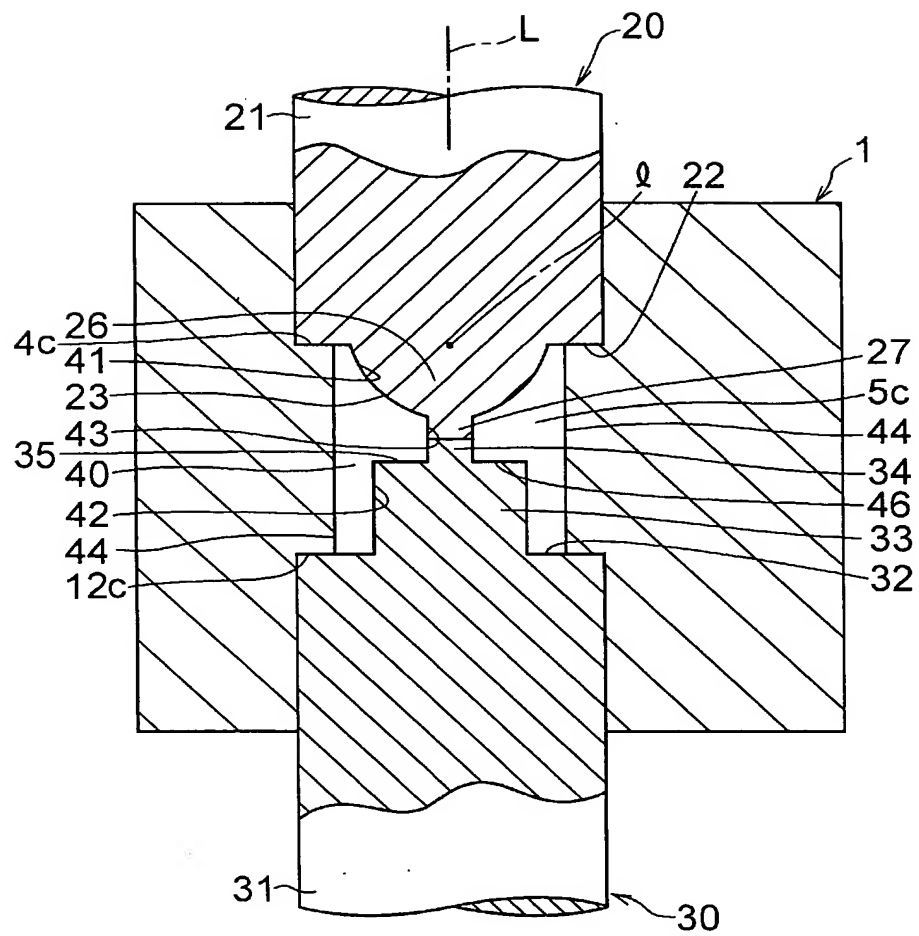
FIG. 4





4 / 16

FIG. 6



5 / 16

FIG. 7

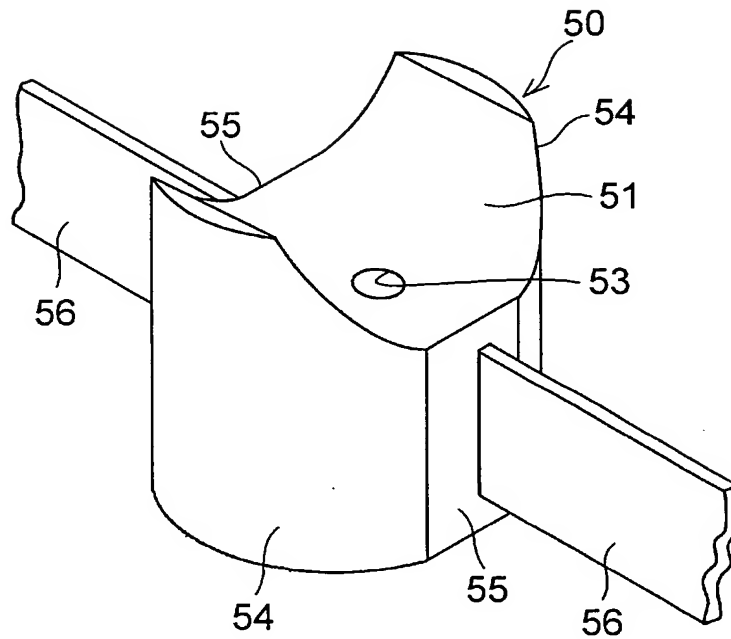
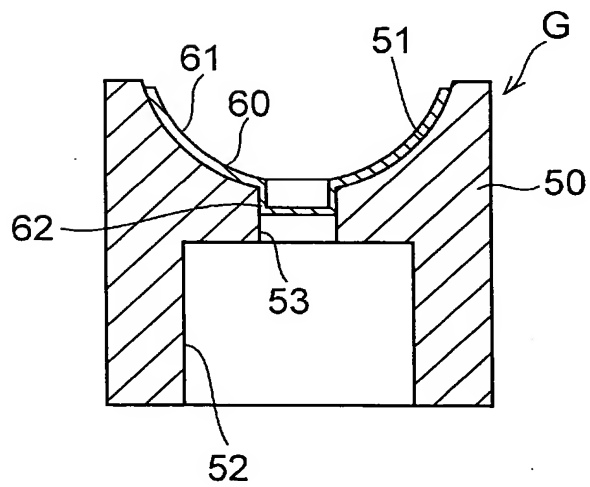


FIG. 8



6 / 16

FIG. 9

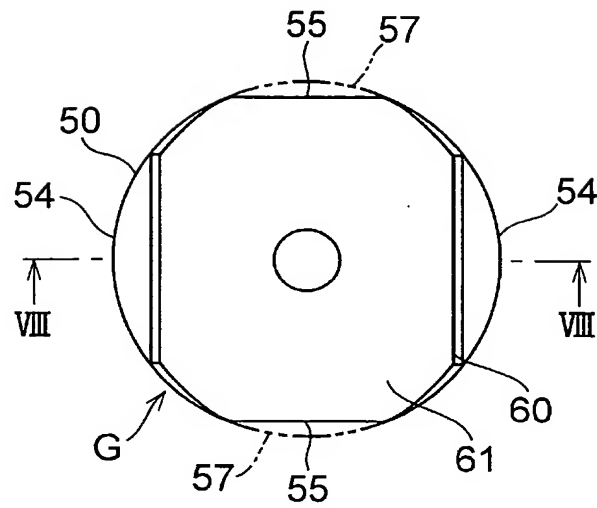
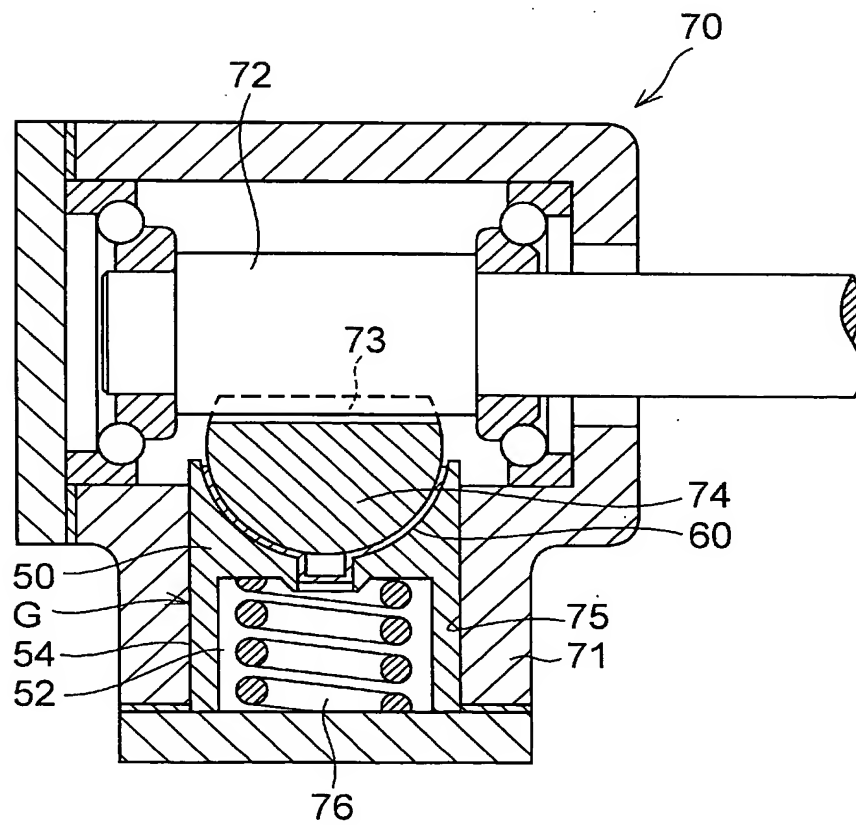


FIG. 10



A detailed cross-sectional diagram of a semiconductor device. The structure consists of several stacked layers and internal features. At the top, there is a layer labeled 80 with diagonal hatching, followed by a layer 81. Below these is a thick layer 4c with diagonal hatching. A dashed horizontal line labeled L indicates a specific level or interface. On the left side, a vertical feature 9c contains sub-components 86, 87, 103, 95, and 108. In the center, there are two rectangular structures 106 and 105, with 104 positioned below them. To the right, another vertical feature 11c contains sub-components 82, 84, 85, 87, 88, and 108. The bottom section includes a layer 90 with diagonal hatching at the very base, and other layers labeled 91, 92, 93, and 94. Various other labels like 100 and 12c point to different structural elements.





FIG. 15

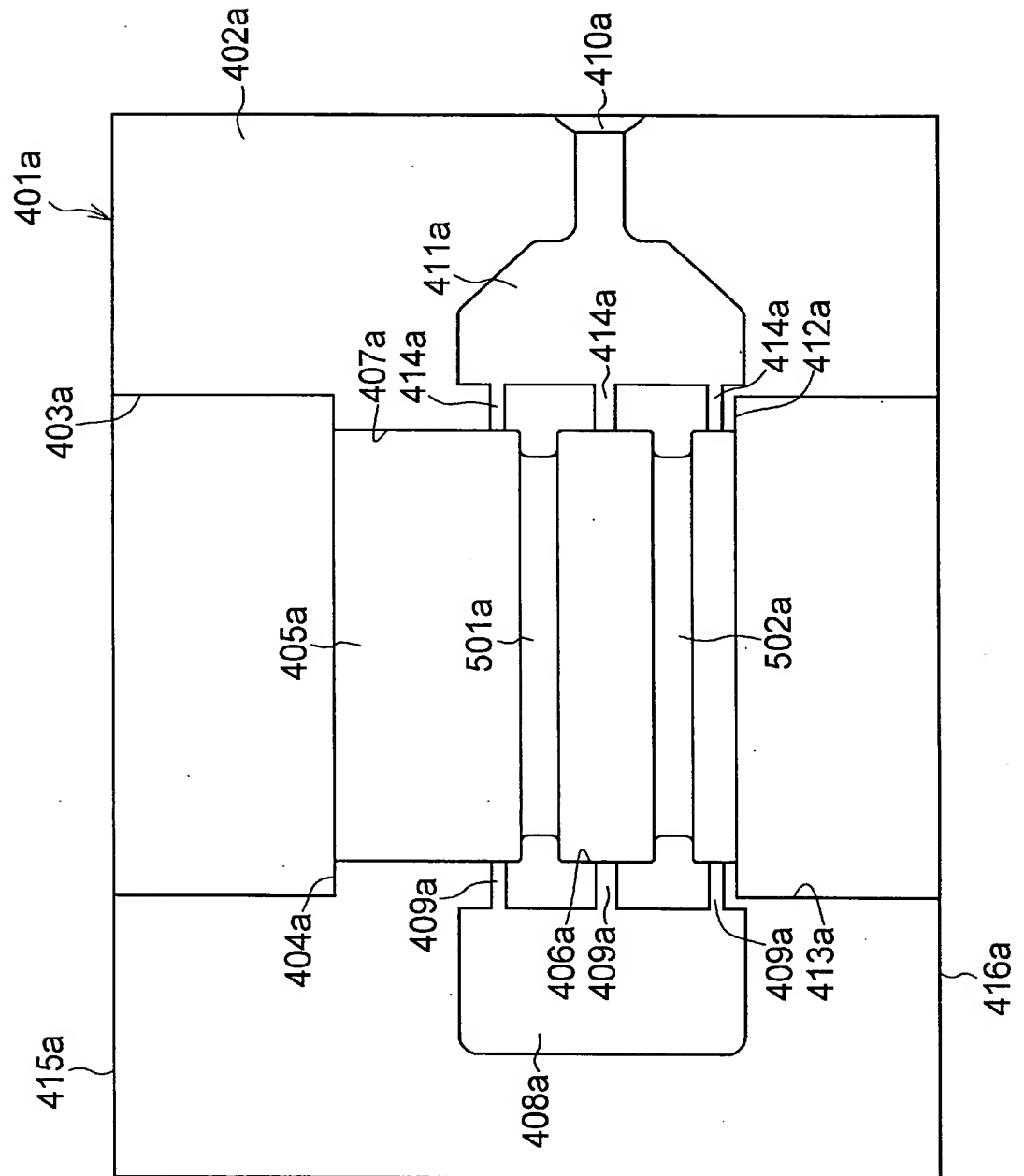


FIG. 16

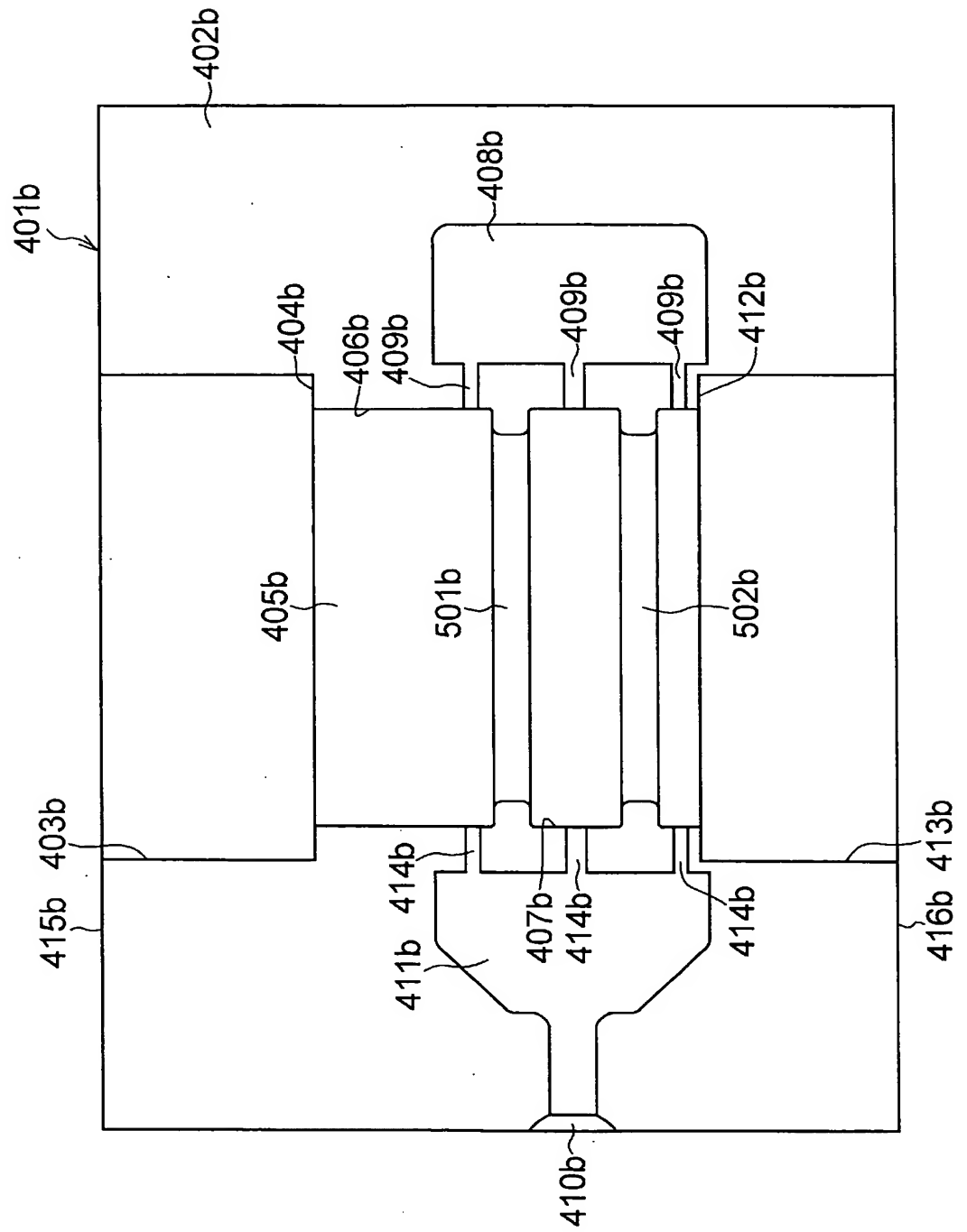
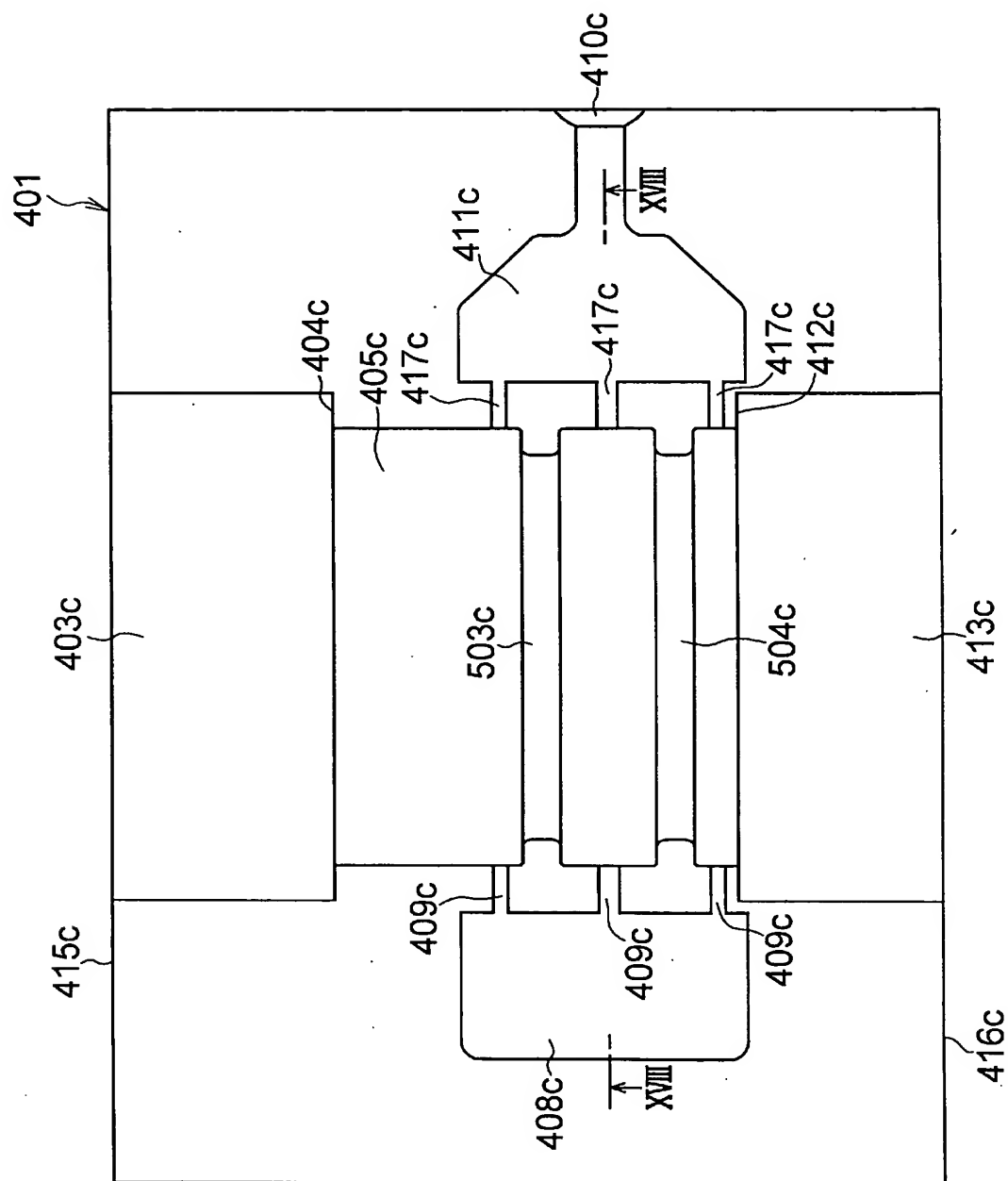


FIG. 17



12 / 16

FIG. 18

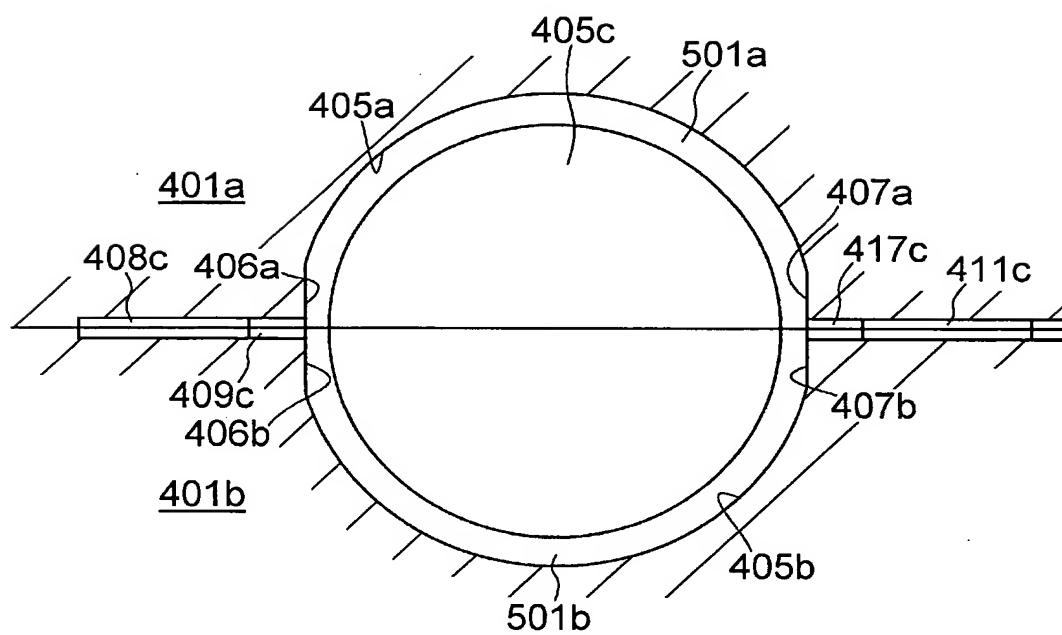


FIG. 19

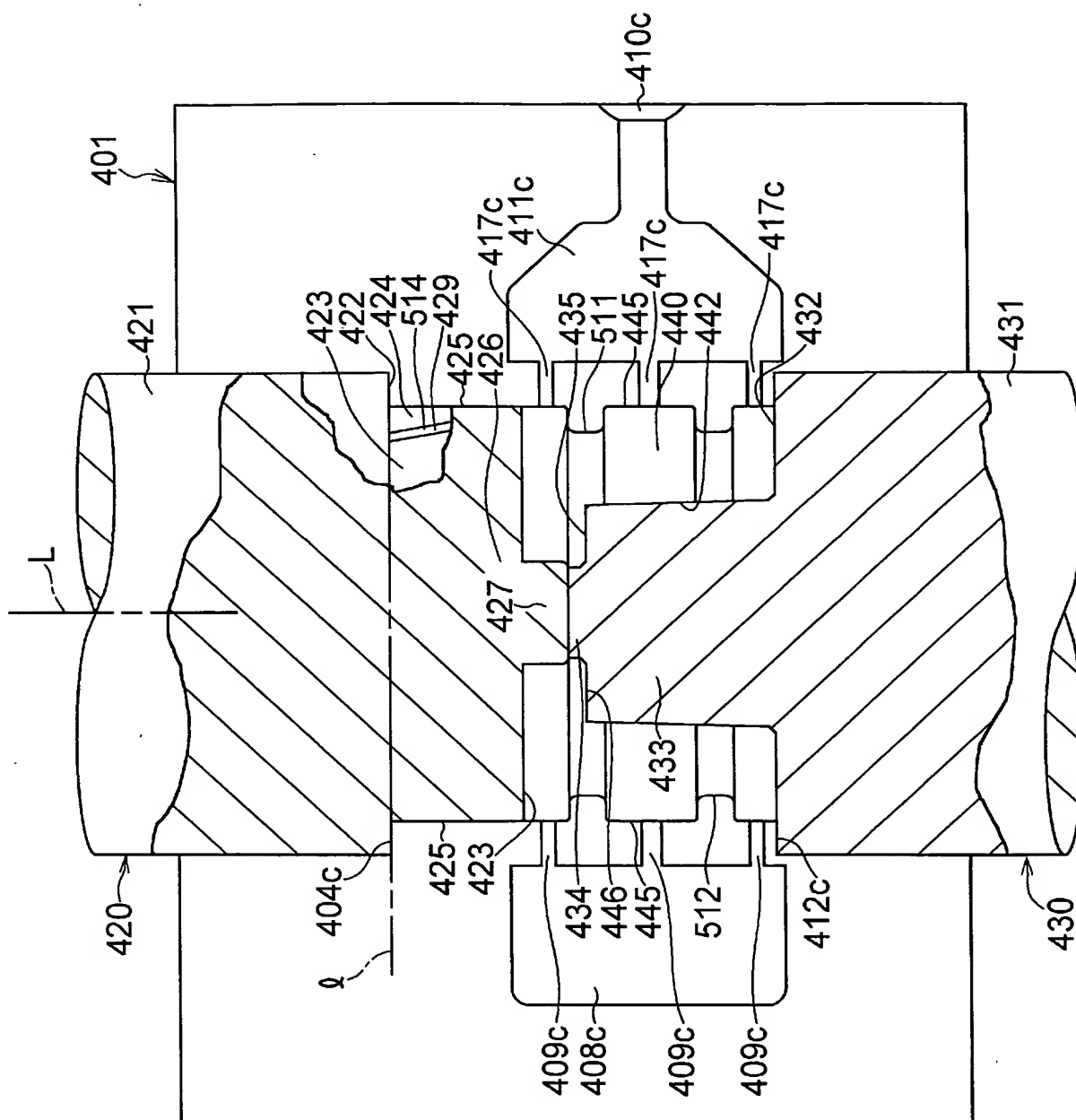
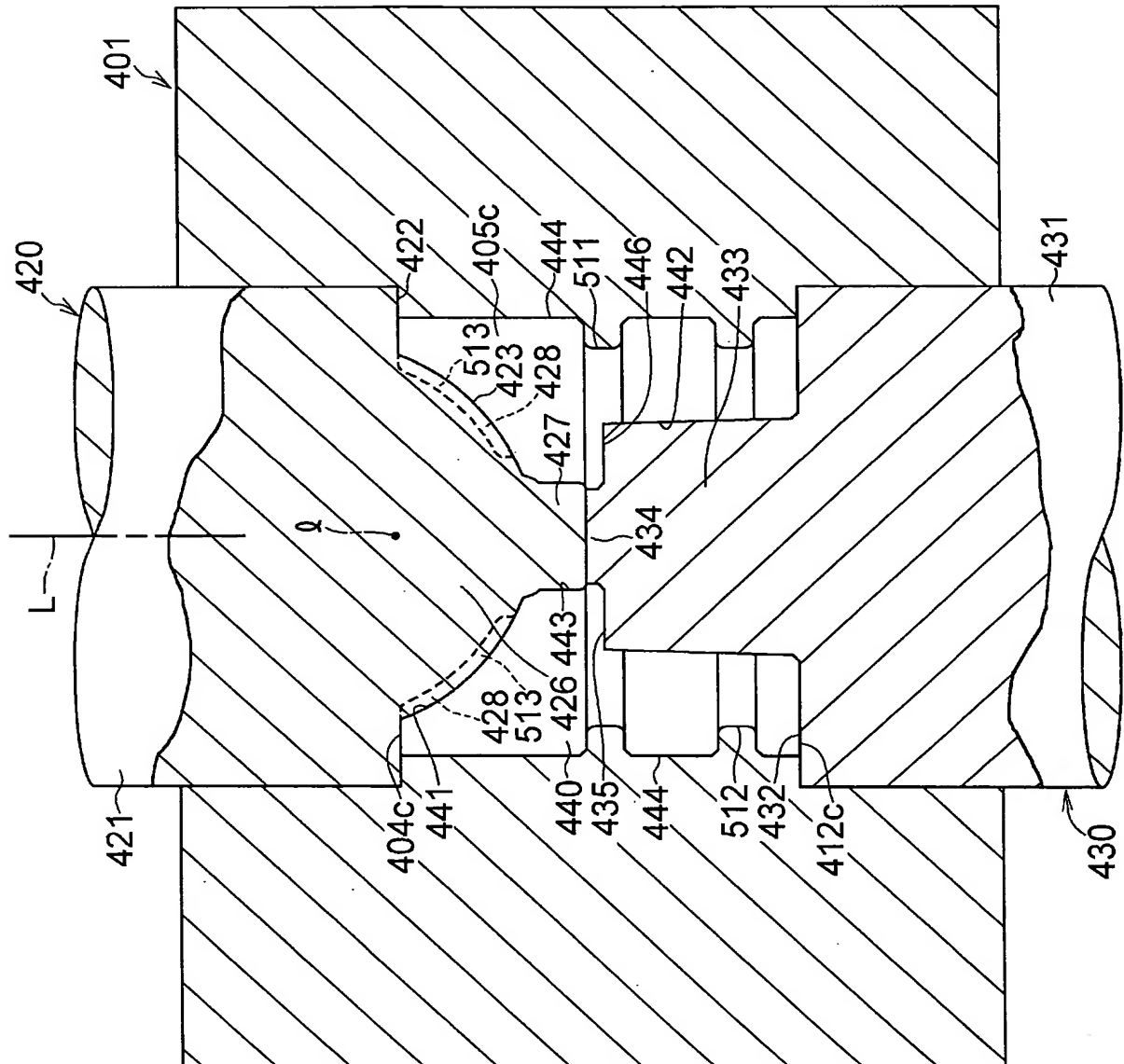


FIG. 20



15 / 16

FIG. 21

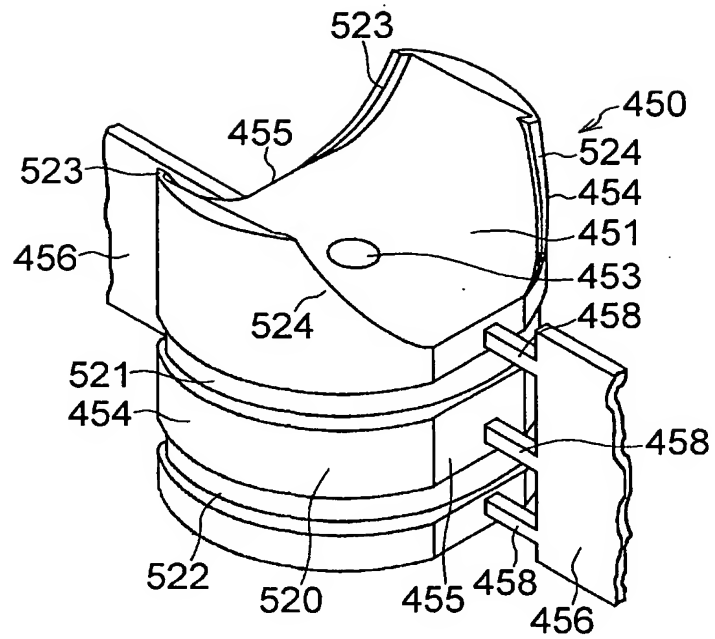
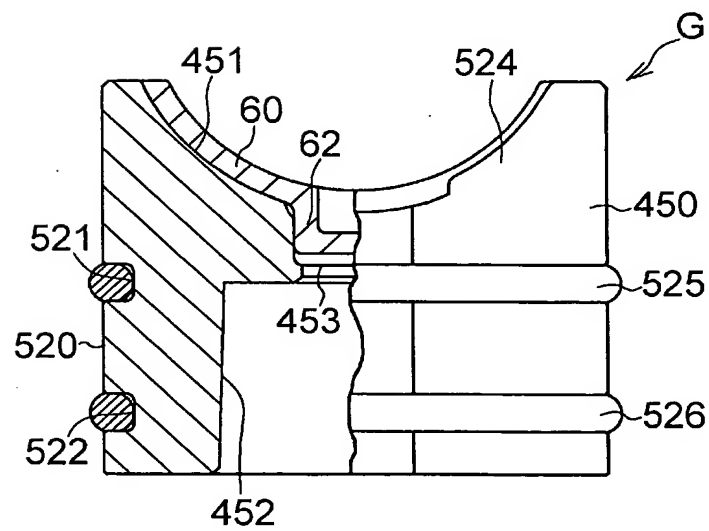


FIG. 22



16 / 16

FIG. 23

